EAST - [10682110 interconnect for FeRAM.wsp:1]

File View Edit Tools Window Help

- Pending
- Active
  - L11: (2) 6426249.pn.
  - L12: (0) 6734459.URPN.
  - L13: (6) ("5369286" | "5604145" | "5719416" | "5786134" | "6284798" | "629
  - L16: (69) (((((first (lower bottom)) adj (contact electrode)) same ((second (upper top)
  - L17: (116) (((side lateral$4) with ((plug interconnect$4) near9 (((through penetrat$4 c
  - L18: (185) 16 17
  - L19: (4) 6201726.URPN.
  - L20: (36) ("4700457" | "4860254" | "4888733" | "4914627" | "5031144" | "51
  - L21: (49004) (((ferroelectric ferro adj electric)) MRAM FeRam FRAM)
  - L22: (1) 10/682110
- Failed
- Saved
  - (1) 09/948877
  - (1738) "KONINKLIJKE PHILIPS".as.
  - (4197362) contact electrode
  - (5244713) first
  - (5380257) lower bottom
  - (4912834) second
  - (4607721) upper top
  - (1208449) plug interconnect$4
  - (10021459) (through penetrat$4 contact$4 reach$4 extend$4)
  - (541644) stack$4
  - (1) 10/682110
  - (158004) (first (lower bottom)) adj (contact electrode)

Browse | Queue | Clear

DBs | USPAT; US PGPUB; EPO; JPO; DERWENT; IBM_TDB | Plurals

Default operator: OR | Highlight all hit terms initially

16 17

	U	S	Inventor	Document	Issue	P	Title	Current	CurrentXR	Retrieval	S	C	P	4	5	6	Image Doc.	P
1		☑	Wainrich, Vol	US 6734459	20040	1	Semiconductor memory cell	257/71	257/295;		☑						US 673445	
2		☑	Evans, Thom	US 6201726	20010	2	Ferroelectric memory device structure usefu	365/145	257/E21.00		☑		☑				US 620172	☑
3		☑	Kim, Yun-gi	US 5798134	19980	8	Memory cells with a reduced area capacitor	257/295	257/296;		☑						US 579813	
4			Iijima, Shinpe	US 6664157	20031	6	Semiconductor integrated circuit device and	438/238	257/E21.01		☑		☑	☑			US 666415	☑
5			Lee, Moon-So	US 6576941	20030	1	Ferroelectric capacitors on protruding portio	257/295	257/306		☑		☑	☑			US 657694	☑
6			Geffken, Rob	US 6426249	20020	1	Buried metal dual damascene plate capacitor	438/239	257/E21.00		☑		☑	☑			US 642624	☑
7			Kang, Hee Bo	US 6363004	20020	4	Nonvolatile ferroelectric memory having shu	365/145	257/E21.66		☑		☑	☑			US 636300	☑
8	☑		Yabuki, Moto	US 2004012	20040	1	Semiconductor device	257/758							☑		US 200401	
9	☑		Ikemasu, Shi	US 2004019	20041	5	Highly integrated and reliable DRAM and its	438/202									US 200401	
10	☑		Kweon, Soon	US 2004019	20041	7	Semiconductor memory device capable of pr	257/303									US 200401	

Ready

NUM